Unit in mm

查询"2SC2879A"媒态商BA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2879A

2~30MHz SSB LINEAR POWER AMPLIFIER APPLICATIONS (LOW SUPPLY VOLTAGE USE)

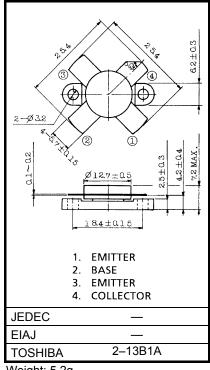
Specified 12.5V, 28MHz Characteristics

Output Power $: Po = 100W_{PEP}$ Power Gain : Gp = 13dBCollector Efficiency $: \eta_C = 35\% \text{ (Min.)}$ Intermodulation Distortion: IMD = -24dB(Max.)

(MIL Standard)

ABSOLUTE MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	45	V
Collector-Emitter Voltage	V _{CES}	45	V
Collector-Emitter Voltage	V _{CEO}	18	V
Emitter-Base Voltage	V _{EBO}	4	V
Collector Current	IC	25	Α
Collector Power Dissipation	PC	250	W
Junction Temperature	Tj	175	°C
Storage Temperature Range	T _{stg}	-65~175	°C



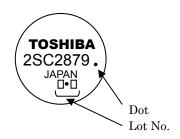
Weight: 5.2g

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

MARKING

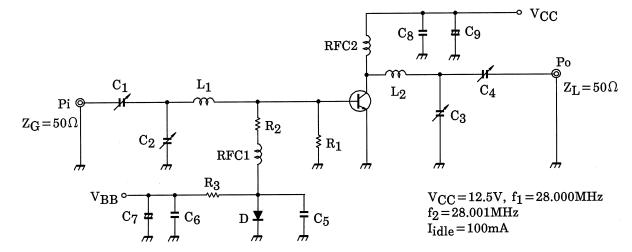


重控制设备AACHARACTERISTICS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = 100mA, I _B = 0	18	_	_	V
Collector-Emitter Breakdown Voltage	V (BR) CES	I _C = 100mA, V _{EB} = 0	45	_	_	V
Emitter-Base Breakdown Voltage	V (BR) EBO	I _E = 1mA, I _C = 0	4	_	_	V
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 10A	10	_	150	
Collector Output Capacitance	C _{ob}	V _{CB} = 12.5V, I _E = 0 f = 1MHz	_	700	_	pF
Power Gain	Gp	V_{CC} = 12.5V, f_1 = 28.000MHz f_2 = 28.001MHz I_{idle} = 100mA Po = 100W _{PEP} .(Fig.)	13.0	15.2	_	dB
Input Power	Pi		_	6	10	W _{PEP}
Collector Efficiency	ηс		35	_	_	%
Intermodulation Distortion	IMD	TO TOUTPER (Fig.)	_	_	-24	dB
Series Equivalent Input Impedance	Z _{in}	V _{CC} = 12.5V, f = 28MHz	_	1.45 -j0.95	_	Ω
Series Equivalent Output Impedance	Z _{out}	$\Delta f = 1 \text{kHz}$, Po = 100W_{PEP}	1	1.45 -j1.0	1	Ω

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南海科科287961度企业



 $C_1, C_2 : 7 \sim 150 pF$

 C_3 , C_4 : $7 \sim 150 \text{pF}$ 2KWV

 $C_5, C_6 : 0.022 \mu F$

 C_7 : $47\mu F$ 10WV

C8 : $0.044 \mu F$

C9 : $100\mu\text{F}$ 50WV

 ${
m L}_{1}$: $\phi 0.8$ ENAMEL COATED COPPER WIRE, 14ID, 4T, 4P

 L_2 : ϕ 1.2 ENAMEL COATED COPPER WIRE, 14ID, 3 1/2T, 3P

RFC1: ϕ 0.8mm EMAMEL COATED COPPER WIRE, 10ID, 9T

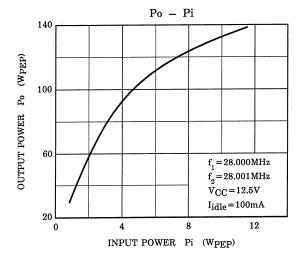
(Ferrite Core TDK K2)

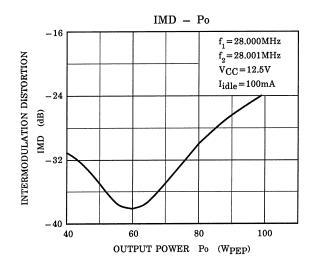
RFC2: ϕ 1.8mm ENAMEL COATED COPPER WIRE, 14ID, 20T

 $R_1 : 10\Omega (1W)$ $R_2 : 2\Omega (1/2W)$

 $R_3 : 10\Omega (5W)$

D : 1S1555





CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.

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查询"2SC2879A"供应商

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20070701-EN GENERAL

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